Serial Number: 10/749,930 Filing Date: December 29, 2003 Title: BODY EFFECT AMPLIFIER

Assignee: Intel Corporation

CLAIMS

The claims are presented herein for the convenience of the Examiner.

- 1. (Original) A circuit comprising:
- a differential pair to receive a differential signal at a bulk input port and to generate an output signal at an output port.
- 2. (Original) The circuit of claim 1 further including a common gate of the differential pair to receive a gate bias voltage.
- 3. (Original) The circuit of claim 1 further including a common source/drain terminal of the differential pair coupled to a current source.
- 4. (Original) The circuit of claim 1 further including an amplifier coupled to the output port.
- 5. (Original) The circuit of claim 1 wherein the output signal is a function of the differential signal.
- 6. (Original) The circuit of claim 1 further including an active load coupled to the drain output port.
- 7. (Original) The circuit of claim 6 wherein the active load includes a transistor having a drain terminal shunted to a gate terminal.
- 8. (Original) The circuit of claim 6 wherein the active load includes a transistor.
- 9. (Original) The circuit of claim 6 wherein the active load includes a transistor having a bulk terminal coupled to a reference node.

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10. (Original) The circuit of claim 6 wherein the active load includes a transistor pair having a common gate.

- 11. (Original) A circuit comprising:
 - a first transistor having a first bulk and a first drain;
 - a first input node at the first bulk; and
 - a first output node at the first drain.
- 12. (Original) The circuit of claim 11 further including a first gate of the first transistor to receive a bias voltage.
- 13. (Original) The circuit of claim 11 wherein the first transistor includes a first source to receive a bias current.
- 14. (Original) The circuit of claim 11 wherein the first transistor includes a first source coupled to a supply voltage.
- 15. (Original) The circuit of claim 11 further including a resistive load coupled to the first output node.
- 16. (Original) The circuit of claim 11 further including a second transistor having a second gate in common with the first gate, the second transistor having a second bulk and a second drain;
 - a second input node at the second bulk; and
 - a second output node at the second drain.
- 17. (Original) The circuit of claim 16 wherein the first transistor and the second transistor include a common source.
- 18. (Original) The circuit of claim 17 further including a current source coupled to the common source/drain.

RESPONSE UNDER 37 CFR § 1.111 AND RESPONSE TO NOTICE OF NON-COMPLIANT AMENDMENT

Dkt: 884.C03US1 (INTEL)

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19. (Original) A method comprising:

biasing a gate terminal of a first transistor in an amplifier;

providing an input signal to a bulk terminal of the first transistor; and

generating a first output signal as a function of the input signal at a first output terminal

coupled to a first drain terminal of the amplifier.

20. (Original) The method of claim 19 wherein biasing includes providing a bias current.

21. (Original) The method of claim 19 wherein providing the input signal includes providing a

first differential input signal to the first transistor of a differential pair and providing a second

differential input signal to a second transistor of the differential pair.

22. (Original) The method of claim 21 further including generating a second output signal at a

second output port coupled to a second drain terminal of the differential pair, the second output

signal generated as a function of the first differential input signal and the second differential

input signal.

23. (Original) The method of claim 21 further including biasing a source terminal of the first

transistor.

24. (Original) The method of claim 23 wherein biasing the source terminal includes providing a

current source.

25. (Original) The method of claim 21 wherein the first transistor is in a saturation mode.

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26. (Original) A communication device comprising:

an antenna having an antenna output;

- a first amplifier including a transistor having a bulk terminal coupled to the antenna output and a bias node coupled to a gate terminal of the transistor; and
 - a second amplifier having an input coupled to a first drain node of the first amplifier.
- 27. (Original) The device of claim 26 wherein the bulk terminal is coupled to the antenna output via a tuner.
- 28. (Original) The device of claim 26 further including a second source terminal of the transistor coupled to a power supply.
- 29. (Original) The device of claim 28 wherein the power supply includes a current source.
- 30. (Original) The device of claim 26 wherein the gate terminal is coupled to a voltage supply.
- 31. (Original) The device of claim 26 further including a resistor coupled to the first drain node and a reference node.
- 32. (Original) The device of claim 26 wherein the first amplifier includes a differential amplifier.
- 33. (Original) A system comprising:
 - a driver having a pair of differential output terminals;
- a receiver having a pair of differential input terminals coupled to the pair of differential output terminals wherein each input terminal is coupled to a bulk terminal of a transistor.
- 34. (Original) The system of claim 33 wherein a gate terminal of each transistor is biased.

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35. (Original) The system of claim 33 wherein the receiver includes an output terminal coupled to a drain terminal of the transistor.

36. (Original) The system of claim 33 wherein the transistor is biased in a saturation region.